

Comprehensive Survey of Ternary Full Adders: Statistics, Corrections, and Assessments

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Abstract: The history of ternary adders goes back to more than six decades ago. Since then, a multitude of ternary full adders (TFAs) have been presented in the literature. This paper conducts a review of TFAs so that one can be familiar with the utilized design methodologies and their prevalence. Moreover, despite numerous TFAs, almost none of them are in their simplest form. A large number of transistors could have been eliminated by considering a partial TFA instead of a complete one. According to our investigation, only 28.6% of the previous designs are partial TFAs. Also, they could have been simplified even further by assuming a partial TFA with an output carry voltage of 0V or V_{DD} . This way, in a single- V_{DD} design, voltage division inside the Carry generator part would have been eliminated and less power dissipated. As far as we have searched, there are only three partial TFAs with this favorable condition in the literature. Additionally, most of the simulation setups in the previous articles are not realistic enough. Therefore, the simulation results reported in these papers are neither comparable nor entirely valid. Therefore, we got motivated to conduct a survey, elaborate on this issue, and enhance some of the previous designs. Among 84 papers, 10 different TFAs (from 11 papers) are selected, simplified, and simulated in this paper. Simulation results by HSPICE and 32nm CNFET technology reveal that the simplified partial TFAs outperform their original versions in terms of delay, power, and transistor count.

Keywords: Computer Arithmetic; CNFET; Multiple-Valued Logic; Ternary Full Adder; Ternary Half Adder

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I. Introduction

Multiple-valued logic (MVL) is a computational approach where there are more than just two truth values. In a more general sense, Fuzzy logic, one of whose intentions is to represent uncertain information, is an extension of MVL to infinite possibilities. Both concepts are in contrast with the traditional binary logic, which is founded upon dualism. Therefore, MVL systems are more compatible with real-world situations and human needs. Jan Lukasiewicz created the first MVL system in 1920. Since then, MVL and Fuzzy logic have been viable alternatives to traditional systems. Nowadays, Fuzzy logic is widely used in natural language processing (NLP) and many other artificial intelligence applications [1, 2]. Fuzzy sets are also broadly used to describe imprecise or vague data [1].

Additionally, at the hardware level, MVL on-chip buses have been proved to be promising [3, 4]. What they do is facilitate the transmission of more information over a bus line. Furthermore, triple- and quad-level cell (TLC and QLC) flash memories are currently being used in industry [5]. They mostly benefit from high data density and low costs. Finally, quantum devices and computers are inherently multivalued [6].

Addition is one of the four basic arithmetic operations. Lying on the critical path, an adder is responsible for almost every calculation inside an arithmetic logic unit (ALU). As a result, its improvement enhances the performance of the entire system. The design of ternary half and full adders (THAs and TFAs) has been a popular subject over the past years. Circuit designers have deployed various logic styles and technologies to reach high-speed, low-power, area-efficient THAs and TFAs. Speed, power consumption, and area are the three main evaluating factors in very large-scale integration (VLSI) design.

Transistors, including bipolar junction transistors (BJTs) and field-effect transistors (FETs), have always been inseparable electronic components from analog and digital circuits. Since there are more than two voltage levels in MVL, multi-threshold transistors are essentially needed for the detection of different voltage levels. Although multi-threshold CMOS (MTCMOS) exists [7], it does not provide the high flexibility required for MVL circuit design. After the advent of carbon nanotube FETs (CNFETs) [8], MVL circuitry has soared in popularity because the threshold voltage of the CNFET device is adjustable by the diameter of carbon nanotubes (CNTs). Most of the literature's ternary and quaternary arithmetic circuits are based on this emerging nanoscale technology.

There are only few brief reviews of the design of ternary logic circuits in the literature [9, 10]. However, to the best of our knowledge, there is not any particular review of ternary adders. We got motivated to undertake a review of TFAs mainly because:

1. There is not any review of TFAs, although there are plenty of published papers about them.
2. The given TFAs in the previous articles have been compared to a limited number of competitors. Hence, the efficiency level of the presented TFAs compared to a wider range of competitors is unknown.
3. The simulation setup in one paper is different from the simulation environment in others. For example, TFAs have been simulated by using different input waveforms. It is impossible/unfair to compare the results when the conditions are not equal.
4. Real simulation test-beds have been neglected in most of the previous papers. For instance, almost all prior TFAs have been simulated without employing any input buffer or a reasonable output load. Therefore, the simulation results reported in these papers are not entirely valid. Besides, a complete input pattern is required to estimate maximum cell delay precisely; however, an incomplete input pattern, missing a large number of transitions, has been used in the previous works. Thus, it is uncertain whether the reported values are truly representative of cell delay or not.

Furthermore, ternary adders usually have a large number of transistors. Circuit designers have always targeted a design with fewer transistors. However, most of the previously presented TFAs are not in their simplest form. The authors could have eliminated more transistors and simplified their designs to a further degree. This has been the second motivation for writing this paper to make a few corrections to some of the previous designs. The following is the synopsis of our main objectives for writing this paper:

1. To obtain statistical information about the number of TFAs whose structures are not in their simplest form. This number can reveal how challenging the design of a TFA might be despite its apparent simplicity.
2. To show how some of the TFAs whose structures are not in their optimal form can be simplified.
3. To simulate TFAs in a realistic simulation test-bed and achieve more accurate results.

Also, we are going to answer the following main research questions:

1. Which design methodologies have previously been used in the literature, and with what prevalence?
2. Are the prior designs in their simplest form? If not, how can we simplify them even further?
3. What are the unresolved issues?

The rest of the paper is organized as follows: A statistical and technical literature review is conducted in Section 2. Section 3 describes how the final TFAs are selected and simplified. Circuit analyses and simulation results in different scenarios are provided in Section 4. Finally, Section 5 concludes the paper.

II. Literature Review and Background

A. Research Method and Bibliographic Information

This paper undertakes a comprehensive literature review of ternary adder cells till the end of 2022 to display the trajectory of this discipline. We have searched reputable publishers such as IEEE, ACM, IET, Elsevier, Springer, Wiley, Taylor & Francis, Emerald, etc for papers in which a new single-digit THA or TFA has been proposed. The Google Scholar website has also been exploited to expand our search results. “Ternary full adder” and “Ternary half adder” were the two major keywords for this purpose.

We have found 125 related papers [11-135], 20% of which have been published in IEEE journals. To be more specific, there are 15 IEEE Transactions [11-25], five IEEE Access [26-30], and two JSSC papers [31, 32]. The other two papers have been published by IEEE ELECTRON DEVICE LETT [33] and IEEE OJ-NANO [34]. Furthermore, CSSP (Springer) [35-42] and MICROELECTR J (Elsevier) [43-50] with eight papers each, and INT J ELECTRON (Taylor & Francis) [51-55] and IET CIRC DEVICE SYST (IET/IEE) [56-60] with five papers each are the journals with the highest number of publications relevant to the subject of THAs and TFAs in other publishers. IEEE ISMVL, with 11 papers [61-71], is the one that stands out among conferences. Figure 1 shows more detailed statistical information in this regard.

There is almost an equal number of THA and TFA papers in the literature (Fig. 2(a)). Additionally, 91 papers out of 125 have been published in journals (Fig. 2(b)). Finally, Fig. 2(c) shows that there has been an upward trend towards the design of THA and TFA circuits in recent years.

B. Statistical Information about Design Techniques

When it comes to technical issues and implementation methods, we can categorize ternary adders in several different ways (statistical information can be found in Fig. 3):

- *Technology* (Fig. 3(a)): Early designs were based on BJT transistors. Then, being the dominant technology in the industry for decades, metal-oxide-semiconductor FET (MOSFET) has been used in 15.2% of the previous designs. However, it is the CNFET technology that with more than 65% contribution excels in popularity. This popularity is mostly because of its high flexibility in threshold adjustment. Other popular technologies are graphene nanoribbon FET (GNRFET) [34, 47, 60, 75, 76] and memristor [22, 23, 26, 63, 77-80]. A fusion of two technologies has sometimes been exploited.

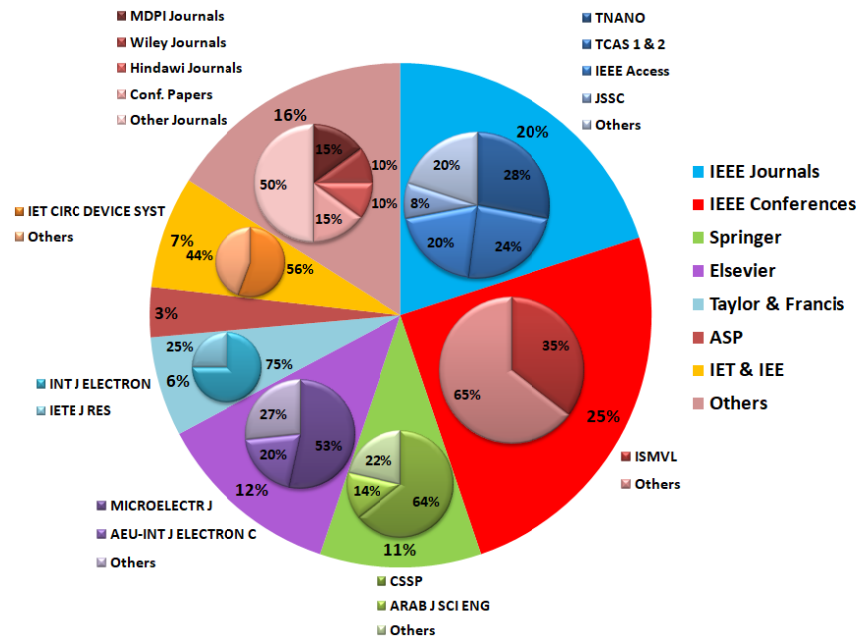


Fig. 1. Papers presenting THAs and TFAs in different publishers and journals/conferences.

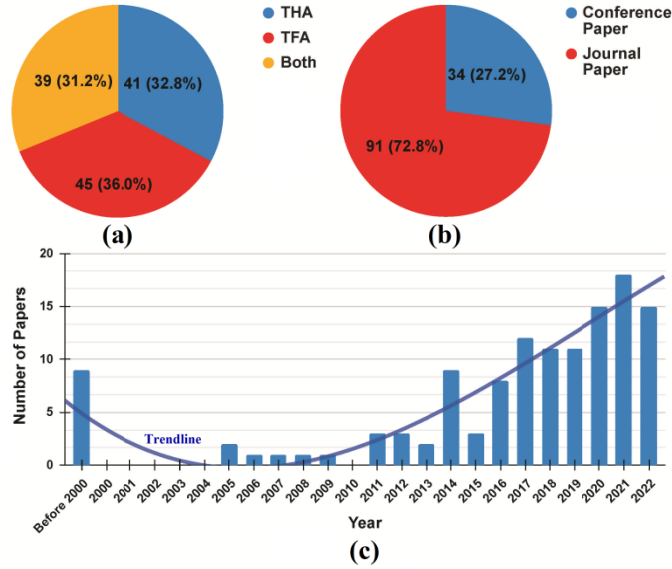


Fig. 2. Papers, (a) Proposing THA, TFA, or both, (b) Conference versus journal papers, (c) Number of papers per year.

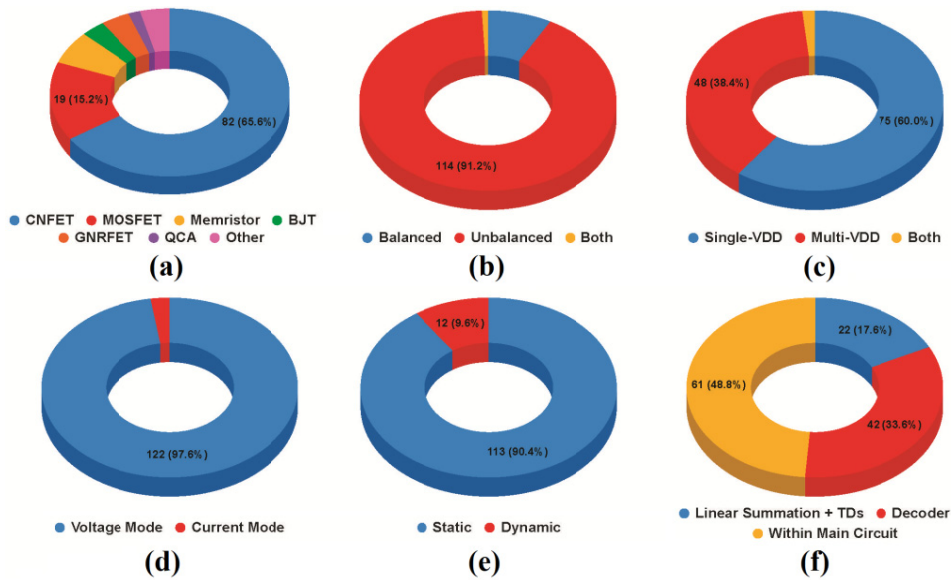


Fig. 3. Statistical information about, (a) Utilized technology, (b) Balanced versus unbalanced, (c) Single- V_{DD} versus multi- V_{DD} , (d) Static versus dynamic, (e) Voltage mode versus current mode, (f) Input decoding methods.

- *Balanced vs. Unbalanced* (Fig. 3(b)): There are two ways to define ternary digits (trits) in base 3: *i*) Balanced (or signed) with the number set $\{-1, 0, +1\}_3$, and *ii*) Unbalanced (or unsigned) with the number set $\{0, 1, 2\}_3$. The latter is the extended version of binary logic and has been considered in more than 91% of the papers.
- *Single- V_{DD} vs. Multi- V_{DD}* (Fig. 3(c)): The unsigned trits, 0, 1, and 2, are represented by $0V$, $\frac{1}{2}V_{DD}$, and V_{DD} , respectively in digital electronics. The additional voltage level, i.e. $\frac{1}{2}V_{DD}$, can be implemented by either voltage division or an extra power supply. In a single- V_{DD} scenario, the additional voltage is internally generated on a chip by using voltage division between GND and V_{DD} . The occurrence of voltage division is synonymous with static power dissipation. Alternatively, in a multi- V_{DD} scenario, the additional voltage, which is externally generated, needs to be routed throughout the entire chip area. It imposes additional costs and wiring, increases routing complexity, and causes some parasitic effects. Following one of the main targets of MVL, which is wire reduction, 60% of the previous ternary adders are single- V_{DD} designs.

- *Static vs. Dynamic* (Fig. 3(d)): Unlike static logic, where the output value only depends on the values of inputs, the output value of a dynamic circuit also depends upon a clock signal (CLK). The clock signal divides time into two phases. In the first one, the output node is pre-charged (or pre-discharged) regardless of the input values. Then, within the evaluation phase, the output node either keeps its voltage or gets discharged (charged) depending on what the values of the inputs are. This technique can help reduce transistor count. Nonetheless, a dynamic circuit requires an additional CLK signal and confronts cascading and charge sharing problems. 90.4% of the previous designs are based on static logic, and only a few are based on dynamic logic [49, 50, 61, 62, 83, 85, 88-90]. It is worth mentioning that the functionality of quantum-dot cellular automata (QCA) designs is also based on the four clock signals incorporated in this technology [82, 91].
- *Voltage Mode vs. Current Mode* (Fig. 3(e)): In voltage-mode logic (VML), logic values are represented by different voltage levels. Similarly, current levels are representative of different logic values in current-mode logic (CML). CML circuits are usually fast and can be implemented with fewer transistors. However, they dissipate much power, which is a huge downside of this logic family. There are only three CML THAs and TFAs in the literature [66, 93, 94] and the rest rely on VML.
- *Input Decoding Method* (Fig. 3(f)): There must be a way to decode input ternary signals. Some circuits, 33.6%, employ ternary decoders for this purpose. This is the most straightforward method. In a little more complex approach, instead of dealing with ternary inputs individually, the linear sum of input variables is initially obtained in some other circuits, 17.6%. To do so, the input wires are simply connected in current-mode circuits. In voltage-mode circuits, a capacitive network is required. Afterwards, threshold detectors (TDs) detect the logic level. A disadvantage associated with this method is its high sensitivity to noise and voltage variation. In MVL circuits, the entire voltage range has already been divided into several levels, and any further voltage division among the input variables causes even narrower voltage zones. On the other hand, this method can reduce the number of transistors because the linear sum of input variables is coped with cumulatively. Finally, in 48.8% of the designs, input signals are detected inside the main body of the circuit using multi-threshold transistors. Note that multi-threshold transistors are needed in every MVL circuit.

Logic or design styles define the methodologies by which logical functions can be implemented in circuit/transistor level. We classify the existing ternary circuits into 13 main logic styles, most of which are extracted from binary logic. It is also feasible to combine some of the logic styles.

1. In ternary resistor transistor logic (RTL) [11], Fig. 4(a), if both pull-down networks (PDNs) are switched off, the output node is pulled up to V_{DD} through the upper resistor. If PDN1 is ON, the two resistors perform voltage division and the output becomes $\frac{1}{2}V_{DD}$. Finally, PDN2 links the output node to the ground whenever it is meant to be '0'. Compared to the resistor, PDN2 has much lower resistance and can pull the output voltage down near 0V. However, a considerable static current is dissipated in this situation. Thus, this logic style is neither full-swing nor power-efficient.
2. With almost the same structure and characteristics, the resistors in ternary RTL are replaced with constantly switched-on transistors in the ternary pseudo-NMOS logic [136], Fig. 4(b).
3. Similar to the binary CMOS logic style, the ternary counterpart (Fig. 4(c)) is composed of pull-up and pull-down networks (PUNs and PDNs), in which n-type and p-type transistors reside, respectively [12]. When PDN1 and PUN1 are both ON, the two diode-connected transistors perform voltage division, and the output voltage becomes $\frac{1}{2}V_{DD}$. In other conditions, when PDN2 and PUN2 are exclusively activated, the output value becomes '0' and '2', respectively.
4. In ternary dynamic logic [137], Fig. 4(d), the output node is initially pre-charged. Then, within the evaluation phase, it either keeps its previous value or takes a new value depending on the status of the networks. This way, one of the networks in the ternary CMOS logic style is eliminated.
5. In ternary capacitive threshold logic (CTL) [65], Fig. 4(e), the linear sum of input variables is calculated by a capacitor network. Then, the voltage level is detected by using some TDs. The rest of the circuit can be similar to the ternary CMOS logic style but with smaller networks and fewer transistors.

6. A ternary function can be represented in three different ways: *i*) Negative ternary (NT), denoted by $-$; *ii*) Positive ternary (PT), denoted by $+$; and *iii*) Standard ternary (ST). These definitions are exemplified in Table 1 for a ternary inverter (NTI, PTI, and STI). Accordingly, the ST function is the average of the other two definitions. It has been the foundation of the next logic style [56], which is called NT/PT functions in this paper (Fig. 4(f)). After $Output^-$ and $Output^+$ are generated, two transistors divide the voltage and produce the standard output.
7. The dynamic version of the previous logic style, Fig. 4(g), for the elimination of two networks has been suggested in [90]. Two inverters are incorporated in the middle for the higher driveability of the circuit.
8. Differential cascode voltage switch (DCVS) belongs to the differential logic family where two complementary outputs are simultaneously generated. In ternary DCVSL [138], Fig. 4(h), when O_1 and O_2 are equal to V_{DD} and $0V$, respectively, Out_1 is pulled down to the ground, and Out_2 is connected to V_{DD} . The opposite conditions lead to $Out_1='0'$ and $Out_2='2'$. Finally, once $O_1=O_2=V_{DD}$, both outputs (Out_1 and Out_2) are concurrently linked to the ground and V_{DD} . In this case, the middle n-type and p-type transistors, which are constantly ON, perform voltage division, and both outputs become '1'. DCVSL circuits are usually fast, but many transistors are relatively consumed for the production of two outputs.
9. The ternary dynamic DCVSL [139], Fig. 4(i), eliminates two networks from its static version.
10. Pass transistor (PT) is a ubiquitous component for circuit design. In addition, a transmission gate (TG) is like a PT but ensures full-swing signal transmission. A network of PTs and/or TGs can be used to design a circuit (Fig. 4(j)) to have very few transistors.

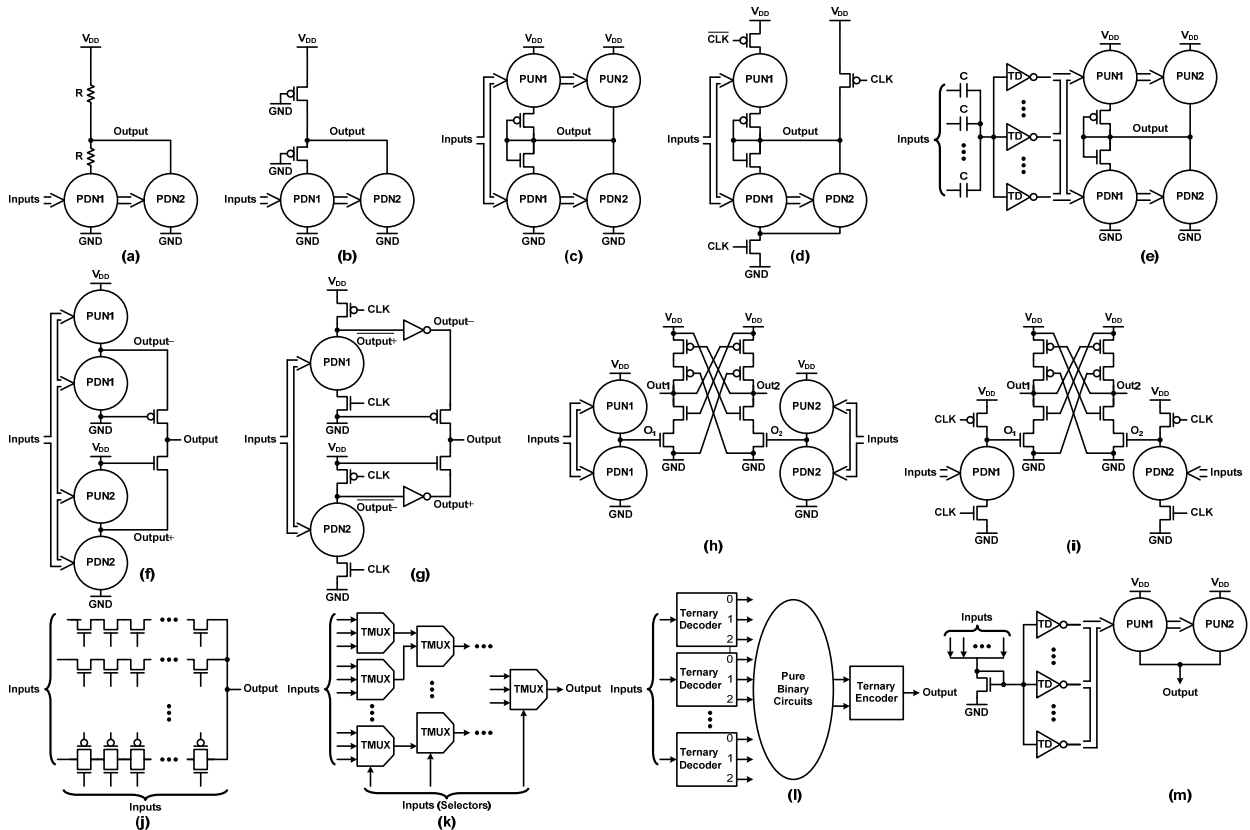


Fig. 4. Well-known logic styles for single- V_{DD} unbalanced ternary circuitry, (a) Ternary RTL [11], (b) Ternary pseudo-NMOS logic [136], (c) Ternary CMOS logic style [12], (d) Ternary dynamic logic [137], (e) Ternary CTL [65], (f) NT/PT functions [56], (g) Dynamic NT/PT functions [90], (h) Ternary DCVSL [138], (i) Ternary dynamic DCVSL [139], (j) MUX-based approach [19], (k) PT/TG, (l) Decoder/Encoder [31], (m) Ternary CML [66].

TABLE I: Truth Table of NTL, PTL, and STI

a	\bar{a}	$\bar{a} +$	\bar{a}
0	2	2	2
1	0	2	1
2	0	0	0

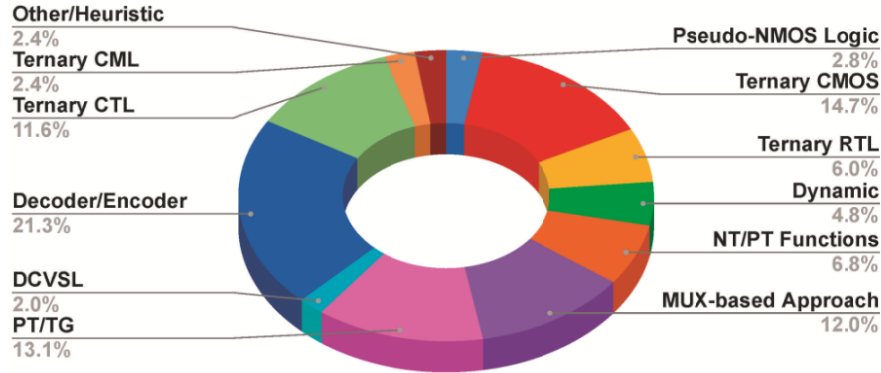


Fig. 5. Statistical information about logic styles.

- Using multiplexers (MUXs) is one of the practical implementation methods of ternary functions. In the MUX-based approach [19], Fig. 4(k), one or more input signals are deemed to be selectors, and the rest are inputs of the multiplexer network. Multiplexers, implemented mainly by PTs/TGs, select the appropriate input value in a hierarchical structure.
- Pure binary circuits can be used after decoding ternary input signals [31] (Fig. 4(l)). The mid-binary circuits can be in any logic style. In the end, a ternary encoder is required to produce a ternary output. There are various designs for ternary decoders and encoders in the literature.
- In ternary current-mode logic (CML) [66], Fig. 4(m), the linear sum of input currents is initially converted to a voltage. Next, some TDs detect the voltage level. Then, a unit of current flows through the output wire if only one of the PUN1 or PUN2 is activated. When both are active, two units of current flow and the output value becomes '2'. Finally, there is no output current and $Output='0'$ if both are off. CML circuits are fast but consume power extensively.

The structures illustrated in Fig. 4 are only the basic/initial block diagrams pertinent to each logic style, and they can have several variations. Besides, in many cases, a combination of two or even more logic styles has been used. Figure 5 shows how prevalent these methods are in designing THAs and TFAs.

C. Complete TFA vs. Partial TFA

The main concentration of this paper is on the design of TFAs. The truth table of a complete TFA, whose input values belong to the set $\{0, 1, 2\}_3$, is shown in Table 2. On the other hand, in a partial TFA (Table 3), the third input never becomes '2' and $c \in \{0, 1\}_3$. It is feasible to show that the complete TFA is required neither for addition nor for subtraction [95]. Moreover, complete TFAs are not required for the construction of column compression ternary multipliers either [95]. Finally, division algorithms are usually based on iterative subtractions or multiplications [140]. As a result, none of the four basic arithmetic operations depends on the complete TFA.

The truth table of the partial TFA (Table 3) has nine fewer rows than the truth table of the complete TFA (Table 2). This brings an excellent opportunity to eliminate many transistors. Nevertheless, partial TFAs have been suggested in only 28.6% of the papers (Fig. 6(a)). Instead of a complete TFA, a partial one could have been presented in the other 71.4% of the previous papers. Therefore, they are not in their simplest form, and they can be simplified to a further degree. Partial TFAs are not a recent innovation, and the first one was presented in 1972 [74].

TABLE II: Truth Table of Complete Ternary Full Adder

a	b	c = 0		c = 1		c = 2	
		Carry	Sum	Carry	Sum	Carry	Sum
0	0	0	0	0	1	0	2
0	1	0	1	0	2	1	0
0	2	0	2	1	0	1	1
1	0	0	1	0	2	1	0
1	1	0	2	1	0	1	1
1	2	1	0	1	1	1	2
2	0	0	2	1	0	1	1
2	1	1	0	1	1	1	2
2	2	1	1	1	2	2	0

TABLE III: Truth Table of Complete Partial Full Adder

a	b	c = 0		c = 1		c = 2	
		Carry	Sum	Carry	Sum	Carry	Sum
0	0	0	0	0	1	0	2
0	1	0	1	0	2	1	0
0	2	0	2	1	0	1	1
1	0	0	1	0	2	1	0
1	1	0	2	1	0	1	1
1	2	1	0	1	1	1	2
2	0	0	2	1	0	1	1
2	1	1	0	1	1	1	2
2	2	1	1	1	2	2	0

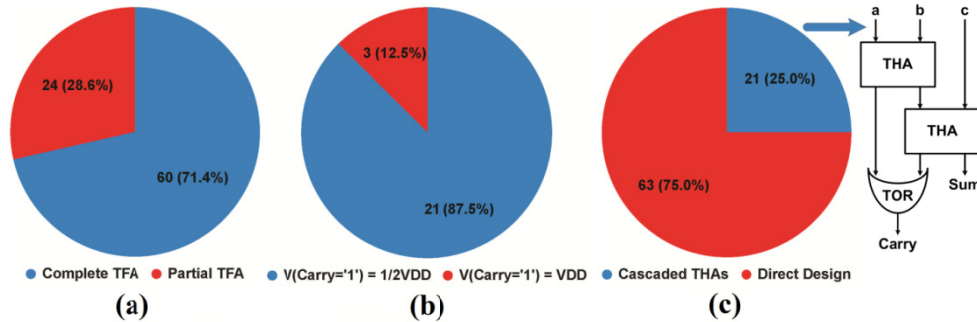


Fig. 6. Statistical information about TFAs, (a) Complete versus partial, (b) $V(\text{Carry}='1') = \frac{1}{2}V_{DD}$ versus $V(\text{Carry}='1') = V_{DD}$, (c) Cascaded THAs versus direct design.

Additionally, the output carry has almost always been implemented by $\{0V, \frac{1}{2}V_{DD}\}$ in partial TFAs. In a single- V_{DD} design, voltage division is inevitably required to obtain $\frac{1}{2}V_{DD}$. Continuous static current flows every time voltage division occurs. This is the main source of high static power consumption of ternary circuits. The more voltage division happens, the more static power dissipates. Alternatively, it is possible to represent $\text{Carry}='1'$ by V_{DD} to decrease the number of times voltage division occurs in a partial TFA. In other words, instead of $\{0V, \frac{1}{2}V_{DD}\}$, the number set $\{0, 1\}_3$ is implemented by $\{0V, V_{DD}\}$ exclusively for the output carry. This way, voltage division is no longer needed for the production of the output carry signal. All we have to do is to change the design of a partial TFA in a way that the received V_{DD} on its third input (input carry signal) is interpreted as logic '1'. It is worth mentioning that the way different voltage levels are interpreted is a conceptual matter. It is up to circuit designers how to map logical values onto voltage levels. Thus, the utilization of $\{0V, V_{DD}\}$ for the output carry is completely feasible and only alters the way of interpretation for this signal. This practical technique has been employed in [96] for the first time and exploited in two other papers [37, 87]. In spite of its usefulness, this technique has been neglected in more than 87% of the previous partial TFAs (Fig. 6(b)).

Eventually, it is always possible to design a full adder by cascading two half adders. 25% of the prior TFAs are based on cascaded THAs, whereas the rest have been designed directly (Fig. 6(c)).

D. Our Final Selection

After the identification and taxonomic classification of the available TFAs, it is time to prune the list with the aim of reaching a limited and reasonable number of designs as a final selection. We decided to choose some TFAs whose main features are identical (e.g. all of them are single- V_{DD} designs, implemented by the same technology, and representing unbalanced ternary logic) while their transistor-level layouts are different. This way, the concentration of the paper would only be on the circuit topology of TFAs. Circuit topology, especially in a single- V_{DD} design where voltage division happens, directly and significantly affects performance and is a crucial factor to deal with. To reach our final selection, we decided to eliminate the following designs from the 84 existing papers in which a new design of TFA has been presented:

- Non-fully transistor-based circuits because we want to concentrate on logic styles and make our comparison independent of the utilized technology. For example, one can compare a memristor-based design with a CNFET-based design, but then the aim of comparison shifts from the topological aspect to the technological factor.
- Multi- V_{DD} designs where another power rail other than V_{DD} and GND is required. Again, it is possible to draw a comparison between single- V_{DD} designs and multi- V_{DD} ones; however, one should keep in mind that HSPICE simulator does not take any of the problematic issues caused by the extra power supply rail into account.
- Balanced ternary whose digits are not in accord with the extended binary number set. Additionally, the extra voltage of $-V_{DD}$ is often required for the implementation of balanced ternary circuits.
- CML designs which consume a lot of power.
- RTL and pseudo-NMOS circuits which are neither power-efficient nor full-swing.
- CTL designs in which the initial voltage division by the capacitor network reduces circuit robustness and makes them sensitive to noise and voltage variation.
- Dynamic logic circuits whose operations are not in accord with static circuits and depend on an external clock other than the input signals.

After eliminating the above varieties, 25 papers remain [13, 17, 18, 21, 35-37, 44, 58, 60, 67, 69, 71, 87, 95, 101-108, 131, 132]. However, many of them follow similar structures. Hence, for the sake of brevity, the next step is to remove TFAs whose structures are repetitive from our list. Our final selection from 11 papers [17, 21, 35, 37, 58, 60, 87, 95, 101-103] forms a reasonable range of TFAs with various design methodologies and logic families. The elimination of TFAs at this stage is because of their similarity to the selected ones. In addition, the same process of simplifying TFAs provided in this paper can easily be applied to any other TFA. Table 4 shows the specifications and simulation results of the 11 selected TFAs. However, as stated before, we cannot compare their delay and power values since they have been simulated in different simulation setups, including different loads, frequencies, and input patterns. Besides, there are no simulation results available in [17] and [87].

III. Selected Ternary Full Adders

As mentioned earlier, the third input signal of a partial TFA, c , never becomes ‘2’. Therefore, this can be exploited to eliminate a multitude of transistors from a complete TFA. Table 5 shows how the simplification process can be done. For example, a p-type transistor whose threshold voltage is *Low* ($Low-V_T$) switches on when the input signal is ‘0’ or ‘1’ ($c = ‘0’|‘1’$). Since c can never take any values other than ‘0’ and ‘1’, the transistor is always ON and can be short-circuited (replaced with a wire). Another example is when a p-type transistor with a high threshold voltage ($High-V_T$) is fed with negated c . In this situation, the transistor turns on when $c = ‘2’$, which never happens. As a result, the transistor is always off, can be eliminated, and replaced with an *open circuit*.

Moreover, to reduce the number of times voltage division happens, we assume that the output carry voltage of a partial TFA equals V_{DD} whenever it is ‘1’ ($V(\text{Carry} = ‘1’) = V_{DD}$). As a result, the next partial TFA in a series of cascaded TFAs receives a binary signal. The way simplification is done is also exemplified in Table 5. A p-type transistor whose threshold voltage is *High* switches on when $c = ‘0’$. In this case, the transistor must be able to distinguish between $c = ‘0’ (=0V)$ and $c = ‘1’ (=V_{DD})$. Thus, the transistor is not removable, but it can be replaced with

a $Low-V_T$ transistor because c is a binary signal. A $Low-V_T$ transistor, with a higher switching speed than a $High-V_T$ transistor, brings about higher performance in most cases.

TABLE IV: Specifications of the Selected TFAs

Design	Logic Style	Technology	Other Characteristics	Simulation Setup ^s	Delay* (ps)	Power* (μ W)
[101] (2012)	Ternary CMOS	CNFET ($L_g=32\text{nm}$)	<ul style="list-style-type: none"> Cascaded THAs Complete TFA 	<ul style="list-style-type: none"> 0.9V Power Supply 100MHz Frequency 26 Input Transitions 2fF Capacitor Load 	386.1	1.462
[35] (2014)	Ternary CMOS	CNFET (L_g N/A)	<ul style="list-style-type: none"> Direct Design Complete TFA 	<ul style="list-style-type: none"> 0.9V Power Supply 100MHz Frequency 26 Input Transitions 2fF Capacitor Load 	166.1	2.209
[102] (2014)	NT/PT Functions	CNFET ($L_g=32\text{nm}$)	<ul style="list-style-type: none"> Cascaded THAs Complete TFA 	<ul style="list-style-type: none"> 0.9V Power Supply 100MHz Frequency 26 Input Transitions Ternary FO4 	43.95	1.472
[103] (2014)	<ul style="list-style-type: none"> Sum: PT-DCVSL Carry: PT/TG 	CNFET ($L_g=32\text{nm}$)	<ul style="list-style-type: none"> Direct Design Partial TFA $V(\text{Carry}='1') = \frac{1}{2}V_{DD}$ 	<ul style="list-style-type: none"> 0.9V Power Supply 250MHz Frequency 306 Input Transitions 2.1fF Capacitor Load 	100	1.45
[58] (2017)	MUX-based Approach + PT/TG	CNFET (L_g N/A)	<ul style="list-style-type: none"> Direct Design Complete TFA 	<ul style="list-style-type: none"> 0.9V Power Supply Frequency N/A Transitions N/A 2fF Capacitor Load 	127.4	1.034
[21] (2020)	NT/PT Functions	CNFET ($L_g=32\text{nm}$)	<ul style="list-style-type: none"> Cascaded THAs Partial TFA $V(\text{Carry}='1') = \frac{1}{2}V_{DD}$ 	<ul style="list-style-type: none"> 0.9V Power Supply 500MHz Frequency 6 Input Transitions Ternary FO4 	269	0.128
[60] (2020)	Decoder/Encoder + Ternary CMOS	CNFET ($L_g=32\text{nm}$)	<ul style="list-style-type: none"> Direct Design Complete TFA 	<ul style="list-style-type: none"> 0.9V Power Supply 1GHz Frequency 26 Input Transitions No Output Load 	≈ 900	≈ 250
[95] (2020) [†]	<ul style="list-style-type: none"> 1st: CMOS 2nd: CMOS 3rd: NT/PT 	CNFET ($L_g=32\text{nm}$)	<ul style="list-style-type: none"> Cascaded THAs & Direct Design Partial TFA $V(\text{Carry}='1') = \frac{1}{2}V_{DD}$ 	<ul style="list-style-type: none"> 0.9V Power Supply 100MHz Frequency 26 Input Transitions Ternary FO4 	108.37 66.168 40.966	1.8916 1.9341 1.4096
[87] (2021)	MUX-based Approach + PT/TG + Ternary CMOS	CNFET (L_g N/A)	<ul style="list-style-type: none"> Direct Design Partial TFA $V(\text{Carry}='1') = V_{DD}$ 	Not Available (N/A)		
[17] (2021)	NT/PT Functions	CNFET ($L_g=45\text{nm}$)	<ul style="list-style-type: none"> Cascaded THAs Complete TFA 	<ul style="list-style-type: none"> 1V Power Supply 100MHz Frequency 26 Input Transitions 1fF Capacitor Load 	No Simulation Results for the Proposed TFA	
[37] (2021)	Ternary CMOS + PT/TG	CNFET ($L_g=32\text{nm}$)	<ul style="list-style-type: none"> Direct Design Partial TFA $V(\text{Carry}='1') = V_{DD}$ 	<ul style="list-style-type: none"> 0.9V Power Supply 250MHz Frequency 64 Input Transitions 2fF Capacitor Load 	238.94	0.98

* Simulation results reported in the original papers.

^s All of the simulations have been performed at room temperature with no input buffers.

[†] Three different designs have been presented in this paper.

Transistor in Complete TFA	Functionality Description	Equivalent Component in Partial TFA
P-Type Transistor		
	Switches on when $c = '0' '1'$ => Always ON	
	Switches on when $c = '0'$	
	Switches on when $c = '2'$ => Always Off	
	Switches on when $c = '2'$ => Always Off	
	Switches on when $c = '0' '1'$ => Always ON	
N-Type Transistor		
	Switches on when $c = '2'$ => Always Off	
	Switches on when $c = '0'$	
	Switches on when $c = '0' '1'$ => Always ON	
	Switches on when $c = '0' '1'$ => Always ON	
	Switches on when $c = '2'$ => Always Off	

A. Designs in [101] and [95]

The complete TFA in [101] (Fig. 7), which is based on ternary CMOS, has been transformed into a partial TFA in [95], where $V(\text{Carry}='1') = \frac{1}{2}V_{DD}$. In this paper, we propose another version where $V(\text{Carry}='1') = V_{DD}$ (Fig. 8). The STI that produces negated c is replaced with a binary inverter (the added transistors are indicated by green color). Moreover, some n-type transistors are crossed out since the voltage division is no longer required in the *Carry* generator part. They were responsible for making $V(\text{Carry}) = \frac{1}{2}V_{DD}$. Table 6 shows how efficient the new partial TFA compared to the previous versions is. It has 32 fewer transistors and a 70.2% lower power-delay product (PDP) than the original design [101]. PDP, calculated by (1), is an important evaluating factor in VLSI design, which makes a balance between delay and power. In addition, because no voltage division occurs in the *Carry* generator part, it consumes 18.2% less power than the one in [95].

$$PDP = \text{Avg}(\text{Power}) \times \text{Max}(\text{Delay}) \quad (1)$$

TABLE VI: Simulation Results for the TFA in [101] and Its Simplified Versions

TFA	Delay (ps)	Power (μW)	PDP (fJ)	#Transistor
Complete [101]	180.70	7.8403	1.4167	106
Partial [95]	125.26	7.6817	0.9622	87
This Paper	67.210	6.2825	0.4223	74
Improvement w.r.t. [101]	$\approx 62.8\%$	$\approx 19.9\%$	$\approx 70.2\%$	$\approx 30.2\%$

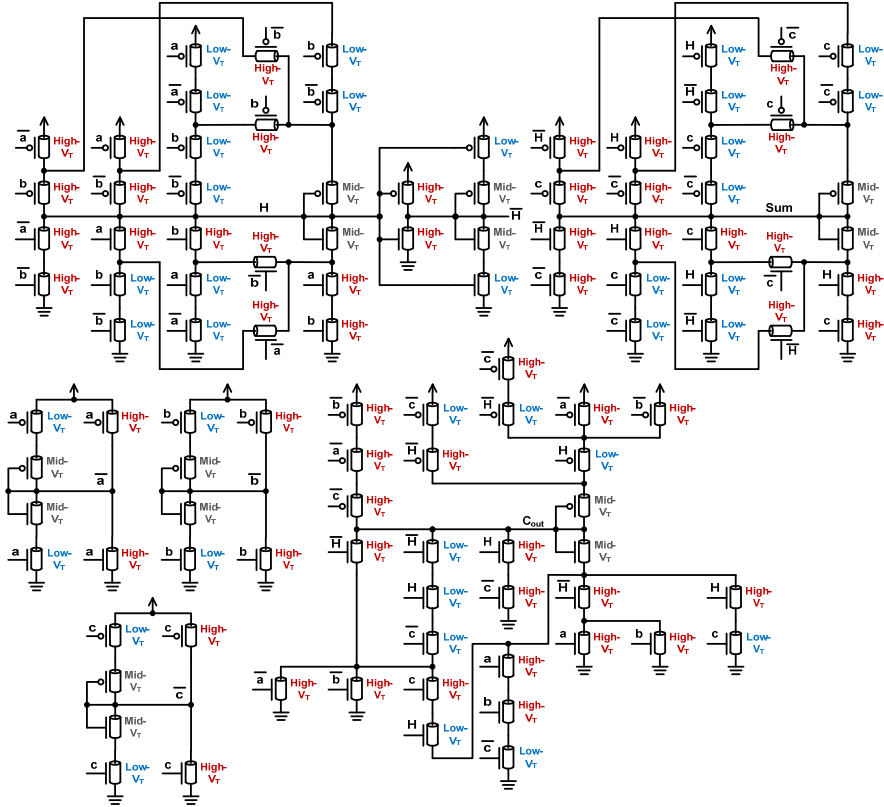


Fig. 7. The complete TFA presented in [101].

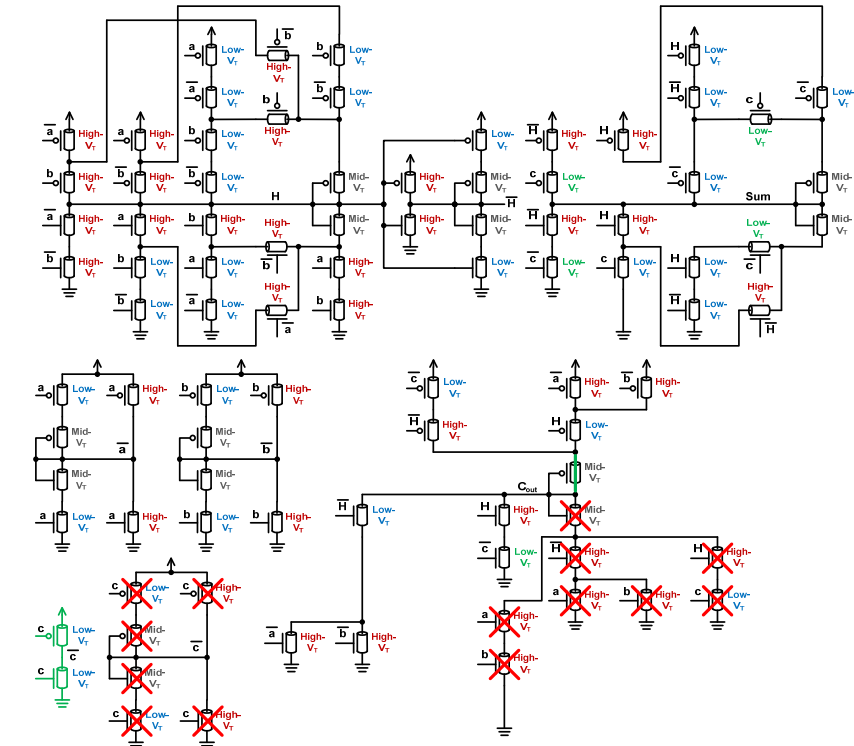


Fig. 8. The partial TFA in [95] is simplified in this paper to reach a new partial TFA, where $V(\text{Carry}='1') = V_{DD}$.

B. Designs in [35] and [95]

Another complete TFA, based on ternary CMOS, has been presented in [35] (Fig. 9). It has been changed into a partial TFA in [95]. We simplify the partial TFA even further by considering $V(\text{Carry}='1')$ to be V_{DD} (Fig. 10). The whole simplification process is precisely similar to what was explained for the previous adder cell. Table 7 shows the simulation results for the prior and new designs. The new partial TFA has 56 fewer transistors than the original one [35] and improves its PDP by 46.3%.

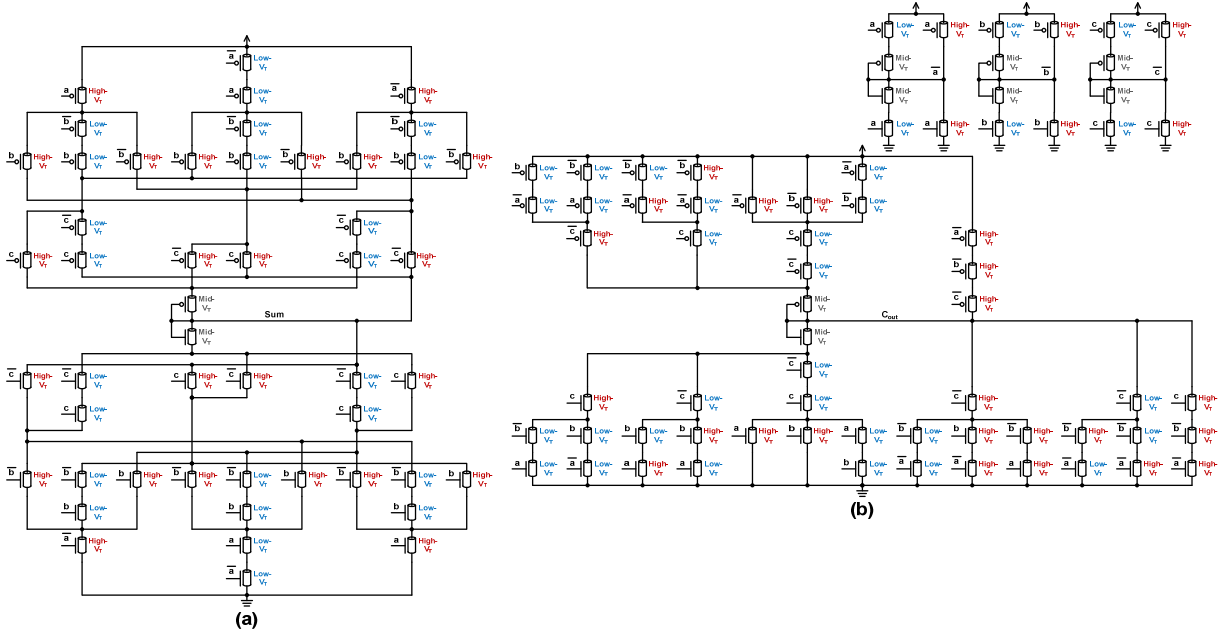


Fig. 9. The complete TFA presented in [35].

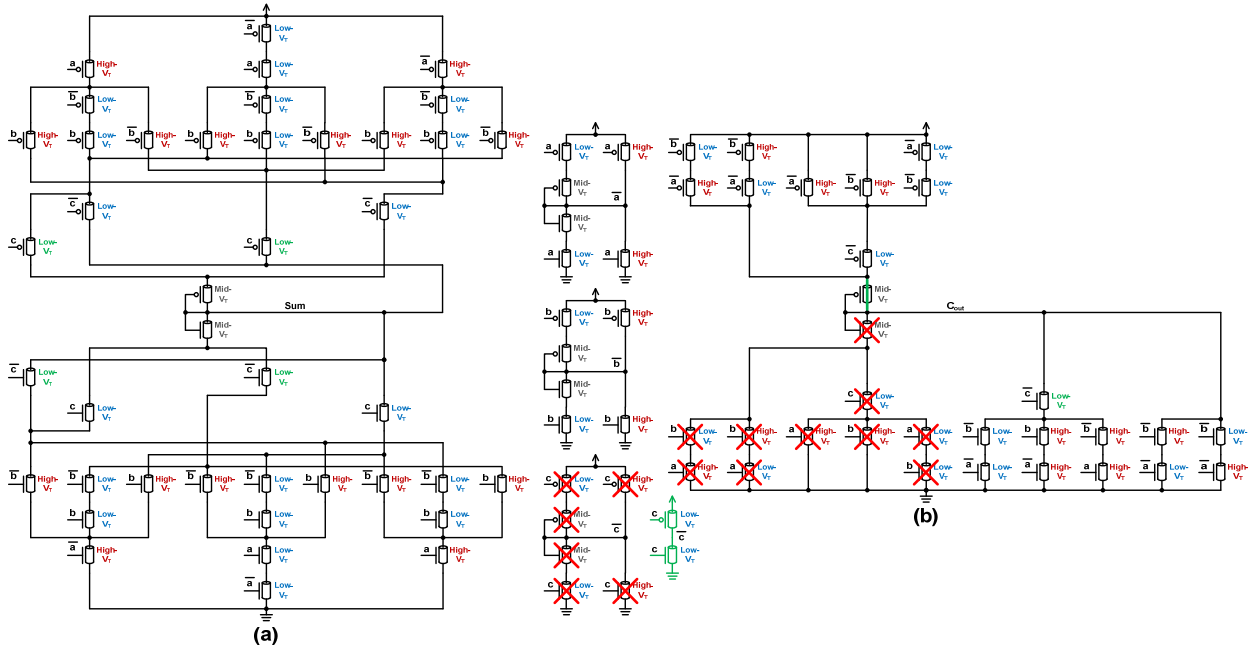


Fig. 10. The partial TFA in [95] is simplified in this paper to reach a new partial TFA, where $V(\text{Carry}='1') = V_{DD}$.

TABLE VII: Simulation Results for the TFA in [35] and Its Simplified Versions

TFA	Delay (ps)	Power (μ W)	PDP (fJ)	#Transistor
Complete [35]	119.14	8.0044	0.9405	132
Partial [95]	117.52	7.3571	0.8646	91
This Paper	111.94	4.5080	0.5046	76
Improvement w.r.t. [35]	$\approx 6.04\%$	$\approx 43.7\%$	$\approx 46.3\%$	$\approx 42.4\%$

C. Designs in [102] and [95]

A complete TFA, which is based on NT/PT functions (Fig. 11), and its partial counterpart have been presented in [102] and [95], respectively. In our proposed TFA (Fig. 12), one (or two) of the duplicated transistors in parallel paths (highlighted by different colors) is/are factored out and eliminated. Simulation results can be seen in Table 8.

TABLE VIII: Simulation Results for the TFA in [102] and Its Simplified Versions

TFA	Delay (ps)	Power (μ W)	PDP (fJ)	#Transistor
Complete [102]	85.024	6.2898	0.5348	142
Partial [95]	66.881	5.8943	0.3942	112
This Paper	58.191	5.3980	0.3141	102
Improvement w.r.t. [102]	$\approx 31.6\%$	$\approx 14.2\%$	$\approx 41.3\%$	$\approx 28.2\%$

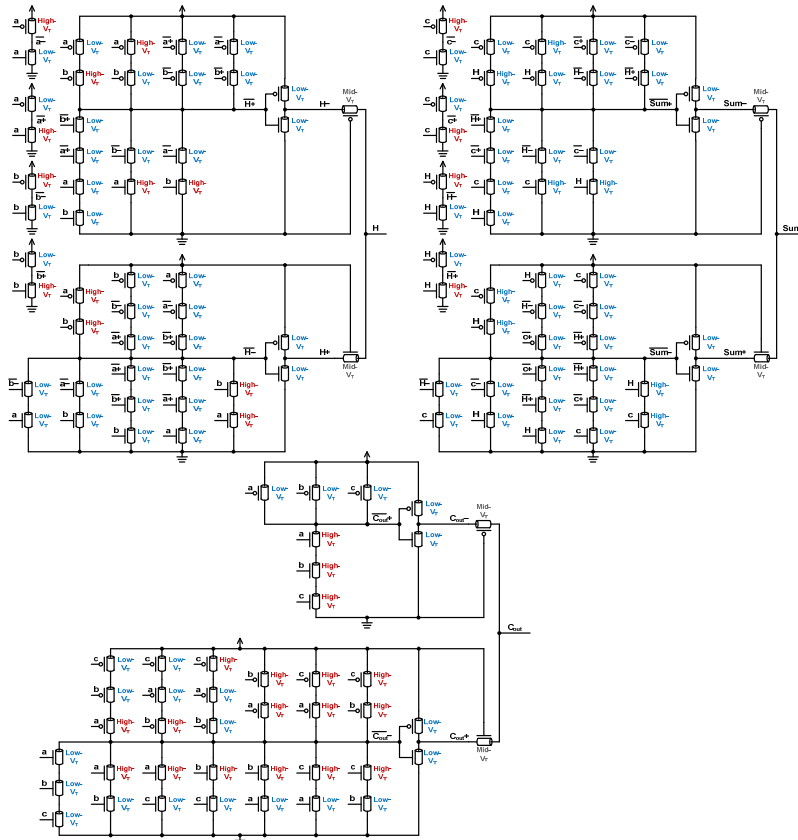


Fig. 11. The complete TFA presented in [102].

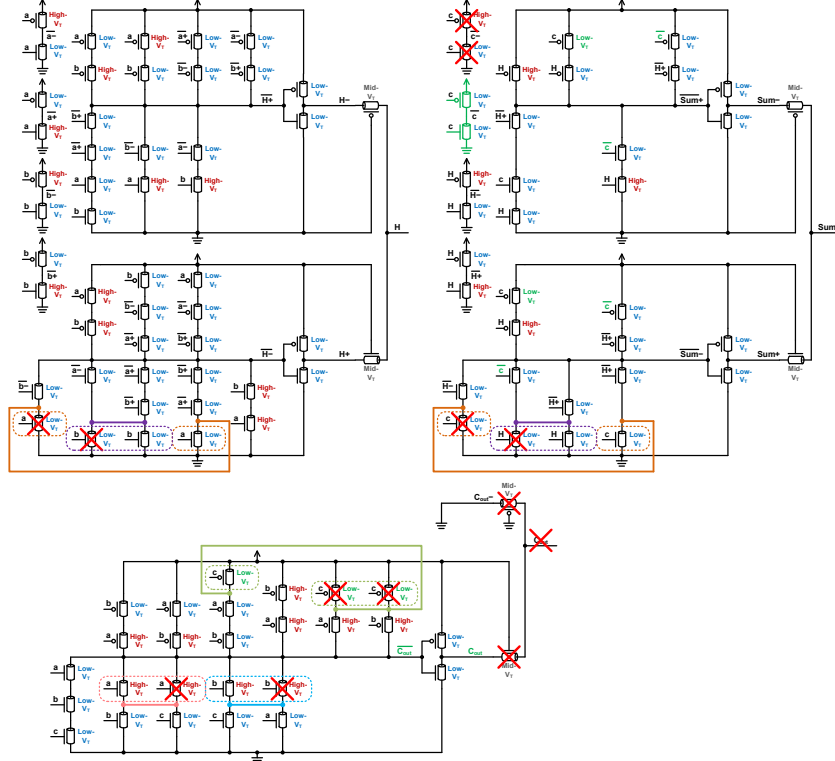


Fig. 12. The partial TFA in [95] is simplified in this paper to reach a new partial TFA, where $V(\text{Carry}='1') = V_{DD}$.

D. Design in [103]

The original ternary adder cell presented in [103] is a partial TFA in which $V(\text{Carry}='1') = \frac{1}{2}V_{DD}$. The first major drawback of this design is that the voltage level of $\frac{1}{2}V_{DD}$ is generated internally by a non-stop voltage division. It is the main source of enormous power dissipation. The second disadvantage is the utilization of n-type PTs that do not pass V_{DD} in a full-swing manner. In our paper, measures are taken to improve its performance (Fig. 13). First, the PT network for the generation of the output carry is fed with V_{DD} , and the corresponding PTs are changed to p-type. This way, V_{DD} is also passed through in a full-swing manner. The middle PTs are changed to TGs as well. Second, the low- V_T n-type PTs in the *Sum* generator part are replaced with ultra-low- V_T ones to alleviate the problem of voltage drop. Table 9 shows how much these modifications improve the performance, although the number of transistors remains unchanged.

TABLE IX: Simulation Results for the TFA in [103] and Its Simplified Version

TFA	Delay (ps)	Power (μ W)	PDP (fJ)	#Transistor
Complete [103]	62.416	9.7617	0.6093	100
This Paper	56.936	5.3516	0.3047	100
Improvement	$\approx 8.78\%$	$\approx 45.2\%$	$\approx 50.0\%$	0%

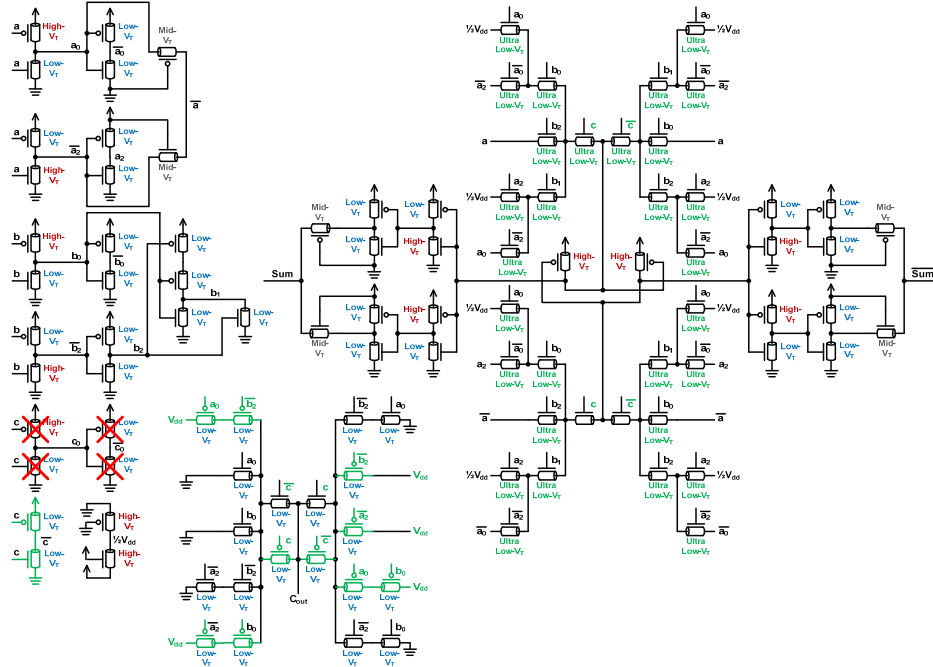


Fig. 13. The partial TFA in [103] is simplified in this paper to reach a new partial TFA, where $V(\text{Carry}='1') = V_{DD}$.

E. Design in [58]

The complete TFA in [58] is almost entirely based on TGs. After some alterations, the new partial TFA (Fig. 14) has 43 fewer transistors and eliminates the continuous voltage division for the production of $\frac{1}{2}V_{DD}$. By considering $V(\text{Carry}='1') = V_{DD}$, the internal generation of $\frac{1}{2}V_{DD}$ is not needed anymore. Besides, instead of a TG, a PT can be deployed when a fixed voltage is supposed to be passed. The simulation results for both versions are presented in Table 10.

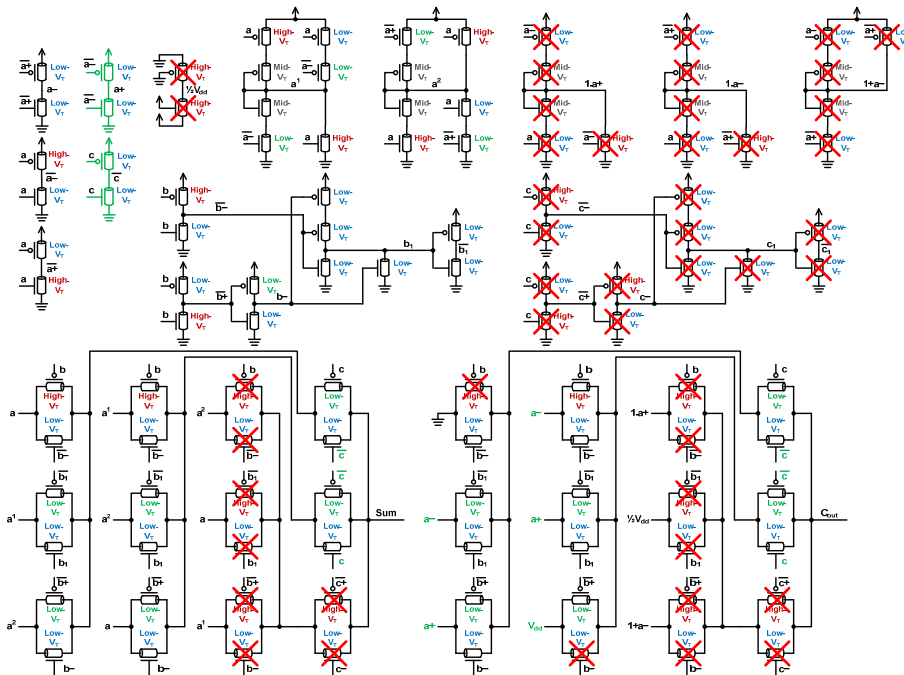


Fig. 14. The complete TFA in [58] is simplified in this paper to reach a partial TFA, where $V(\text{Carry}='1') = V_{DD}$.

TABLE X: Simulation Results for the TFA in [58] and Its Simplified Version

TFA	Delay (ps)	Power (μ W)	PDP (fJ)	#Transistor
Complete [58]	116.79	10.338	1.2074	109
This Paper	90.231	6.1885	0.5584	66
Improvement	$\approx 22.7\%$	$\approx 40.1\%$	$\approx 64.9\%$	$\approx 39.4\%$

F. Design in [21]

The partial TFA in [21] is another design based on NT/PT functions. In our simplified version, since the output carry is deemed either 0V or V_{DD} , three voltage divisions in the Carry generator part are eliminated (Fig. 15). As a result of this simplification, the average power consumption decreases by 26.9% (Table 11).

TABLE XI: Simulation Results for the TFA in [21] and Its Simplified Version

TFA	Delay (ps)	Power (μ W)	PDP (fJ)	#Transistor
Complete [21]	227.82	6.1240	1.3952	106
This Paper	154.63	4.4792	0.6926	78
Improvement	$\approx 32.1\%$	$\approx 26.9\%$	$\approx 50.4\%$	$\approx 26.4\%$

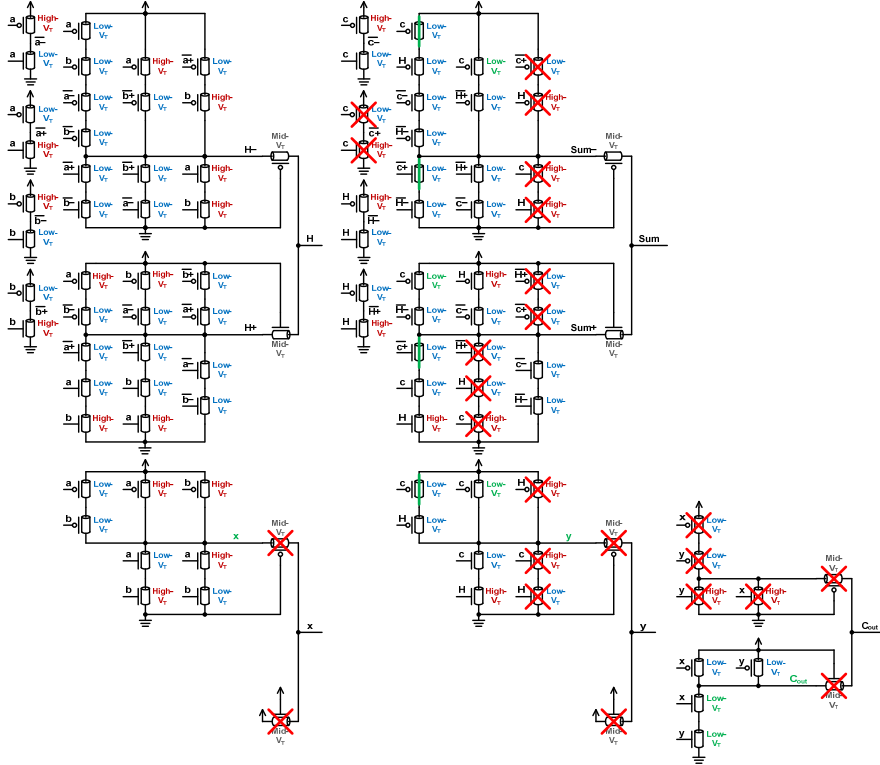


Fig. 15. The partial TFA in [21] is simplified in this paper to reach a new partial TFA, where $V(\text{Carry}='1') = V_{DD}$.

G. Design in [60]

The complete TFA in [60] is an example where the ternary inputs are initially decoded. The decoded signals are binary. However, ternary logic gates have still been used for the main body of the circuit. This is why it has too many transistors (1130 ones), which is not acceptable at all. The authors could have replaced ternary logic gates with binary counterparts. By considering this replacement, changing the whole adder cell into a partial one, and eliminating repetitive AND gates, 864 transistors are deleted in our simplified version (Fig. 16). The simulation results are depicted in Table 12. The original TFA fails to operate at 1GHz input frequency because of its long delay.

TABLE XII: Simulation Results for the TFA in [60] and Its Simplified Version

TFA	Delay (ps)	Power (μ W)	PDP (fJ)	#Transistor
Complete [60]	Failed	Failed	Failed	1130
This Paper	318.49	7.8805	2.5098	266
Improvement	-	-	-	$\approx 76.5\%$

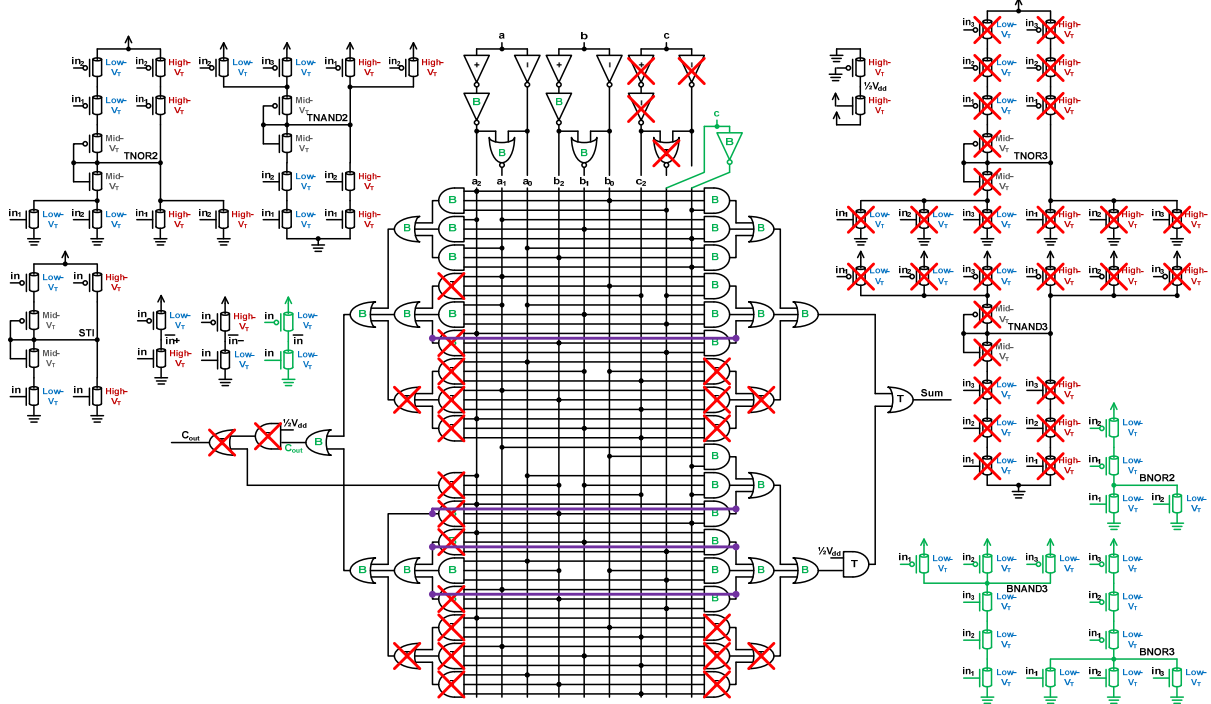


Fig. 16. The complete TFA in [60] is simplified in this paper to reach a partial TFA, where $V(\text{Carry}='1') = V_{DD}$.

H. Design in [87]

The partial TFA in [87], where $V(\text{Carry}='1') = V_{DD}$, is in its ideal form. The only improvement possible to make is to remove four transistors from the original design (Fig. 17). Table 13 shows the simulation results for both versions.

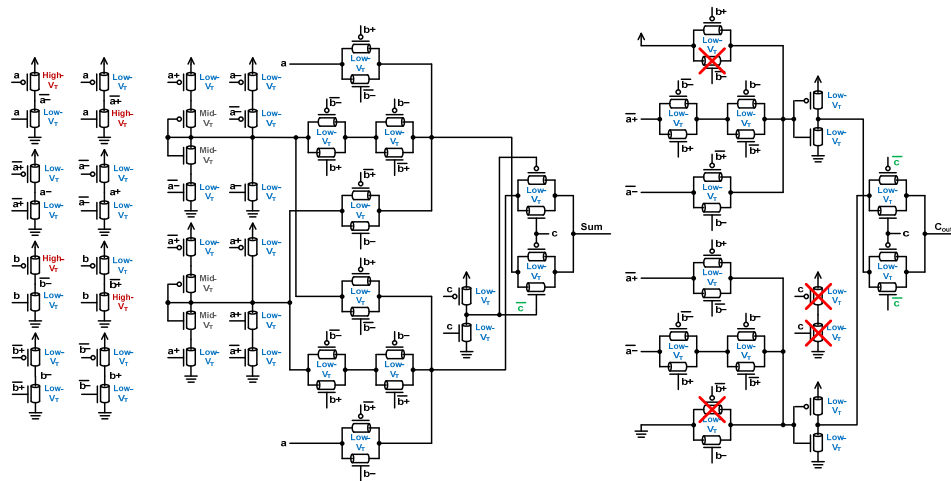


Fig. 17. The partial TFA in [87] is simplified in this paper.

TABLE XIII: Simulation Results for the TFA in [87] and Its Simplified Version

TFA	Delay (ps)	Power (μ W)	PDP (fJ)	#Transistor
Complete [87]	67.556	5.5509	0.3750	78
This Paper	66.665	5.4544	0.3636	74
Improvement	$\approx 1.32\%$	$\approx 1.74\%$	$\approx 3.04\%$	$\approx 5.13\%$

I. Design in [17]

The complete TFA in [17] is simplified in this paper by the elimination of 84 transistors (Fig. 18). Table 14 shows that the simplified version is much faster (24.8%) and more power efficient (22.8%) than the previous version.

TABLE XIV: Simulation Results for the TFA in [17] and Its Simplified Version

TFA	Delay (ps)	Power (μ W)	PDP (fJ)	#Transistor
Complete [17]	91.203	9.2611	0.8446	198
This Paper	68.622	7.1485	0.4905	114
Improvement	$\approx 24.8\%$	$\approx 22.8\%$	$\approx 41.9\%$	$\approx 42.4\%$

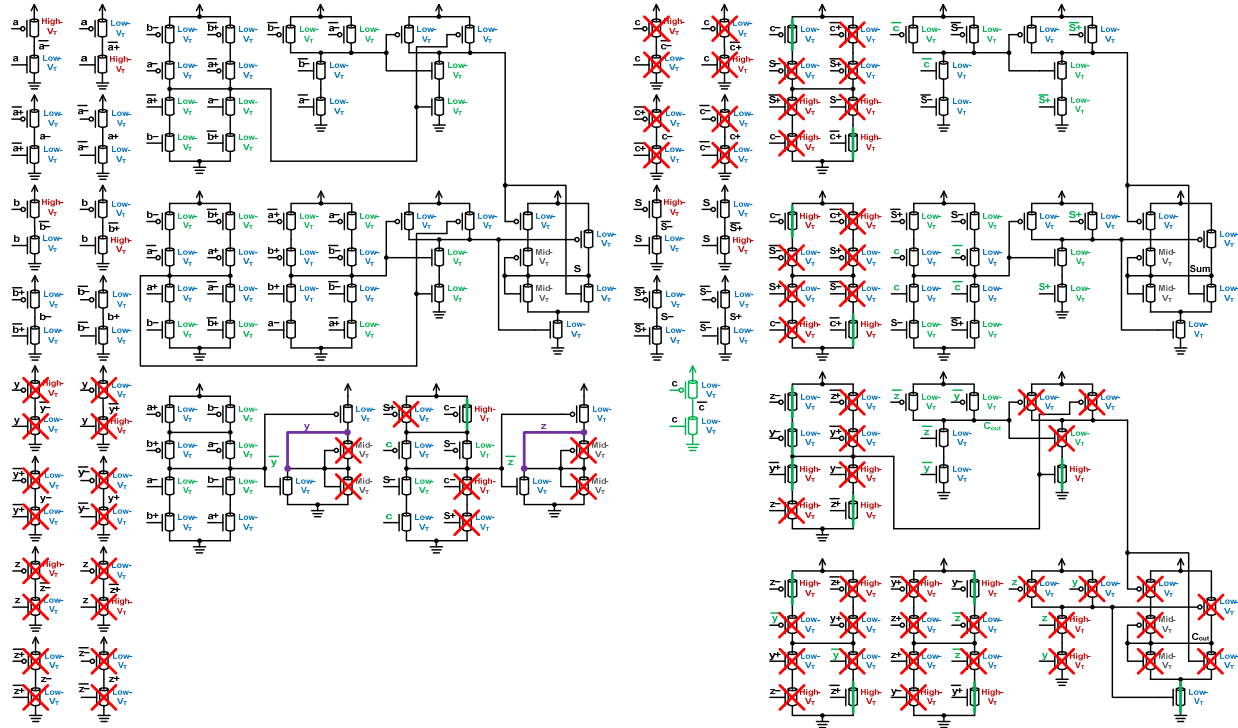


Fig. 18. The complete TFA in [17] is simplified in this paper to reach a partial TFA, where $V(\text{Carry}='1') = V_{DD}$.

J. Design in [37]

The partial TFA in [37], whose simulation results are given in Table 15, is in its simplest form (Fig. 19), and we have not made any specific simplification to this design. However, in spite of being in the simplest form, the output *Sum* is non-full-swing in some input patterns because two n-type (p-type) transistors are placed in the PUN (PDN).

TABLE XV: Simulation Results for the TFA in [37]

TFA	Delay (ps)	Power (μ W)	PDP (fJ)	#Transistor
Partial [37]	165.74	4.1627	0.6899	54

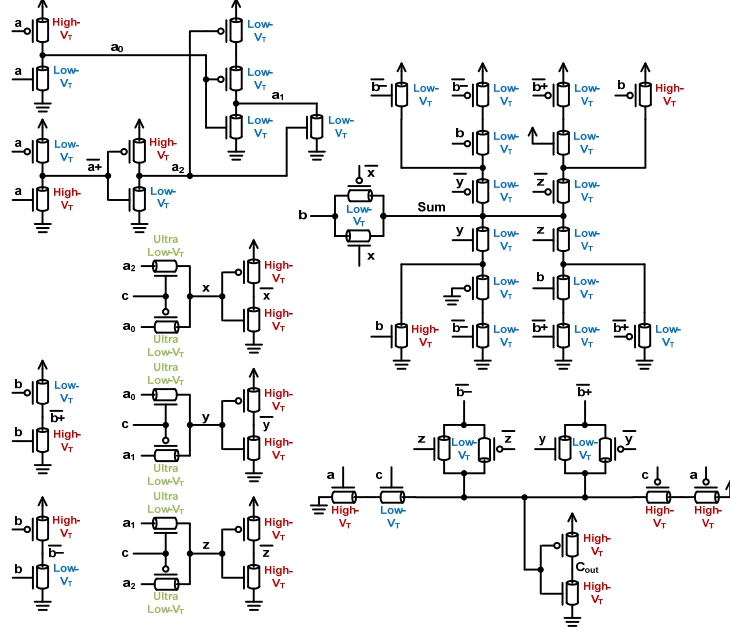


Fig. 19. The partial TFA in [37].

IV. Simulation Results and Comparison

Synopsys HSPICE simulator is the CAD tool utilized in all of the previous papers for transistor-level circuit simulations. The same simulator and 32nm MOSFET-like CNFET library, presented at Stanford University [141], is used in this paper. This standard model includes non-idealities and has been designed for CNFETs with one or more CNT(s) as the channel material. All of the circuits are simulated in a 0.9V power supply at room temperature. Input buffers and ternary fan-out of 4 (ternary FO4) output loads also provide a standard test-bed (Fig. 20(a)), where ideal inputs pass through ternary buffers and non-ideal input signals are connected to the partial TFA under test. None of the previous papers has considered input buffers in their simulation scenarios. Additionally, the complete input pattern, including all transitions (306 ones) with the operating frequency of 1GHz is fed to the circuits (Fig. 20(b)). The maximum delay among the transitions is considered to be the maximum cell delay. Also, the average power consumption during all the transitions is the average power consumption of the cell ($P_{Average}$). The simulation results shown in the previous Section comply with the above conditions.

The chirality vectors for *High- V_T* , *Mid- V_T* , *Low- V_T* , and *Ultra Low- V_T* CNFETs are (10, 0), (14, 0), (19, 0), and (25, 0), respectively. Moreover, all CNFETs are assumed to have three CNTs under their gate terminal. This assumption is in accord with most of the previous papers. In addition, this way, the number of transistors is a close criterion for area assessment. With the aim of vivid and compact illustration, the simulation results for the newly simplified partial TFAs are shown in Table 16 once again. The simplified version of the partial TFA in [103] with the structure of DCVSL excels at delay and PDP. However, the partial TFA in [37], which has the fewest transistors, consumes the least power.

Power dissipation is a major concern in ternary designs, especially single- V_{DD} ones where voltage division for the generation of $\frac{1}{2}V_{DD}$ occurs. As indicated in (2), the total power consumed by a digital circuit (P_{Total} or $P_{Average}$) is the sum of dynamic and static power ($P_{Dynamic}$ and P_{Static}) [142]. In (2), a is the switching activity factor, C is the capacitor load, and f is the operating frequency. To measure static power, the amount of power dissipated while a TFA is in a stable condition (without the occurrence of any transition in the internal and output nodes) is measured by HSPICE. This measurement is repeated for all of the 18 input possibilities of the truth table of the partial TFA (Table 3), and the average amount is considered P_{Static} . For a deeper analysis of power consumption, the elements of power versus different operating frequencies and capacitive loads are shown in Figs. 21 and 22, respectively. The difference between total and static power implies $P_{Dynamic}$. The following are the observations from this trial:

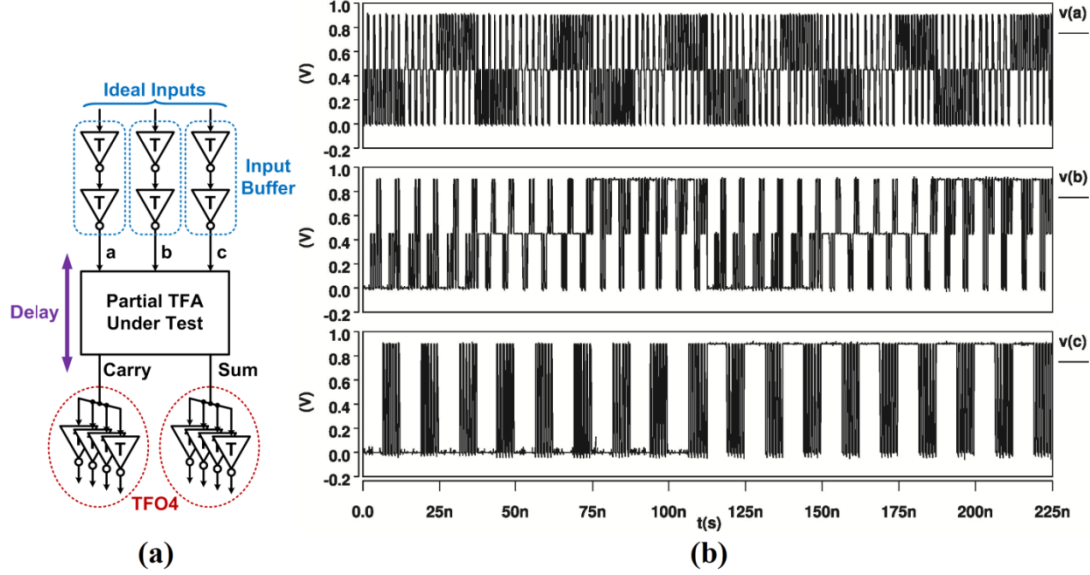


Fig. 20. Simulation setup, (a) Simulation test-bed, (b) Complete input pattern for the simulation of simplified partial TFAs.

TABLE XVI: Simulation Results of the Simplified Single-Digit Partial TFAs

Simplified Partial TFAs of	Delay (ps)	Average Power (μ W)	PDP (fJ)	#Transistor
[101] (Fig. 8)	67.210	6.2825	0.4223	74
[35] (Fig. 10)	111.94	4.5080	0.5046	76
[102] (Fig. 12)	58.191	5.3980	0.3141	102
[103] (Fig. 13)	56.936	5.3516	0.3047	100
[58] (Fig. 14)	90.231	6.1885	0.5584	66
[21] (Fig. 15)	154.63	4.4792	0.6926	78
[60] (Fig. 16)	318.49	7.8805	2.5098	266
[87] (Fig. 17)	66.665	5.4544	0.3636	74
[17] (Fig. 18)	68.622	7.1485	0.4905	114
[37]* (Fig. 19)	165.74	4.1627	0.6899	54

*We have not made any simplification to this design.

$$P_{Total} = P_{Dynamic} + P_{Static} = a.C.f.V^2 + I_{Static}.V \quad (2)$$

- The amount of static power remains almost constant as the operating frequency and capacitive load increase. The result adheres to (2), which shows that P_{Static} is independent of these factors.
- Another noticeable point is that, in most cases, static power is a significant portion of the total power consumption of TFAs.
- $P_{Dynamic}$ (and P_{Total} as a result) for some of the partial TFAs increases with higher intensification than others. This phenomenon is quantified in Figs. 21 and 22 by the slopes of the curves.

Eventually, another simulation scenario for the simulation of the newly simplified partial TFAs is considered. In the second scenario, a 4-digit ripple carry adder (RCA), Fig. 23, is constructed by each of the simplified partial TFAs. Several input patterns that trigger the entire propagation path from the least significant block to the most significant block are fed to the RCA for the assessment of delay. This experiment shows that deploying $\{0V, V_{DD}\}$ for the output carry does not adversely affect the functionality and operation of RCAs. Simulation results for this scenario can be found in Table 17. The RCA with the simplified version of the TFA in [17] excels at delay and PDP. However, the RCA with the partial TFA in [37] consumes the least power.

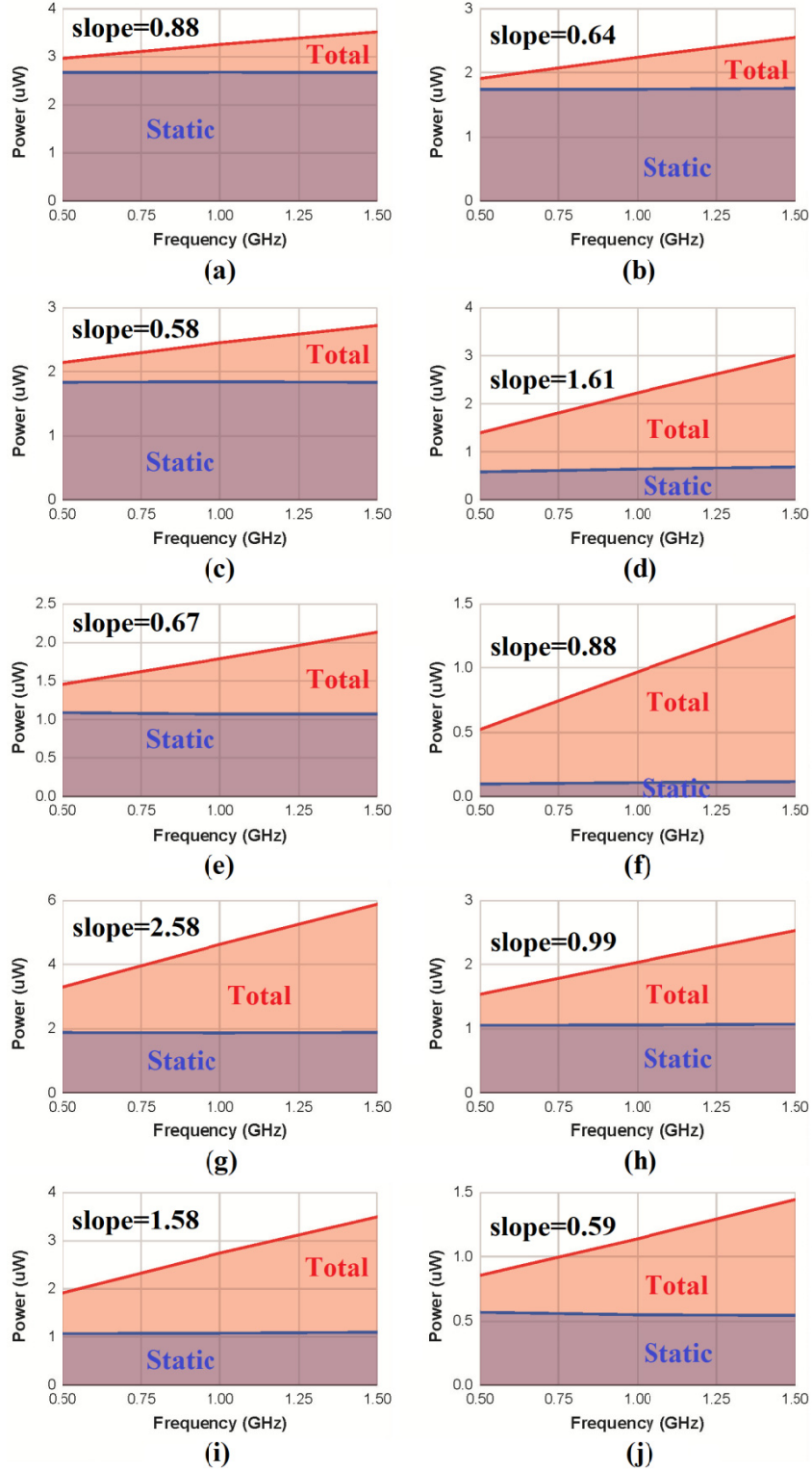


Fig. 21. Power consumption versus operating frequency, (a) [101] - Fig. 8, (b) [35] - Fig. 10, (c) [102] - Fig. 12, (d) [103] - Fig. 13, (e) [58] - Fig. 14, (f) [21] - Fig. 15, (g) [60] - Fig. 16, (h) [87] - Fig. 17, (i) [17] - Fig. 18, (j) [37] - Fig. 19.

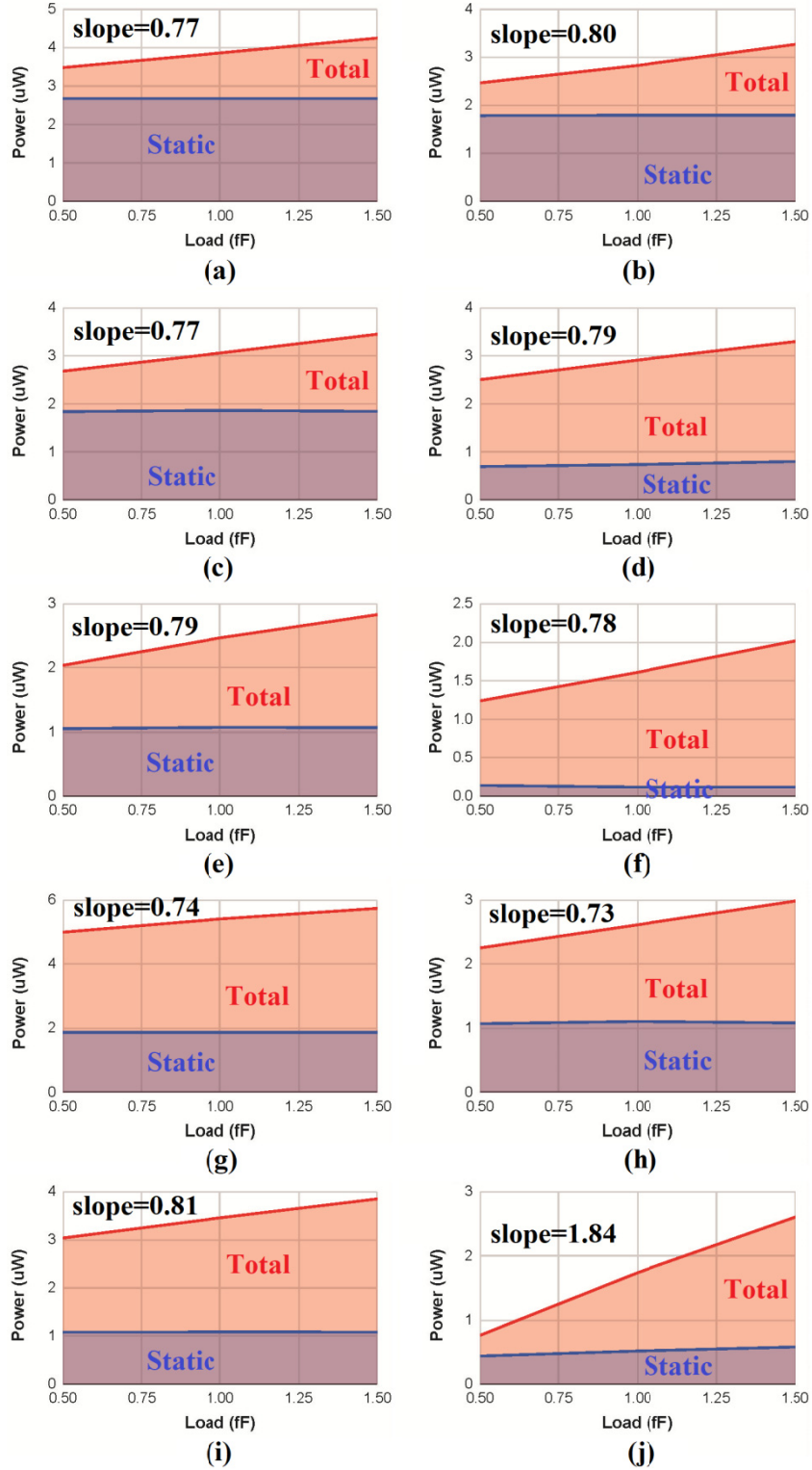


Fig. 22. Power consumption versus capacitive load, (a) [101] - Fig. 8, (b) [35] - Fig. 10, (c) [102] - Fig. 12, (d) [103] - Fig. 13, (e) [58] - Fig. 14, (f) [21] - Fig. 15, (g) [60] - Fig. 16, (h) [87] - Fig. 17, (i) [17] - Fig. 18, (j) [37] - Fig. 19.

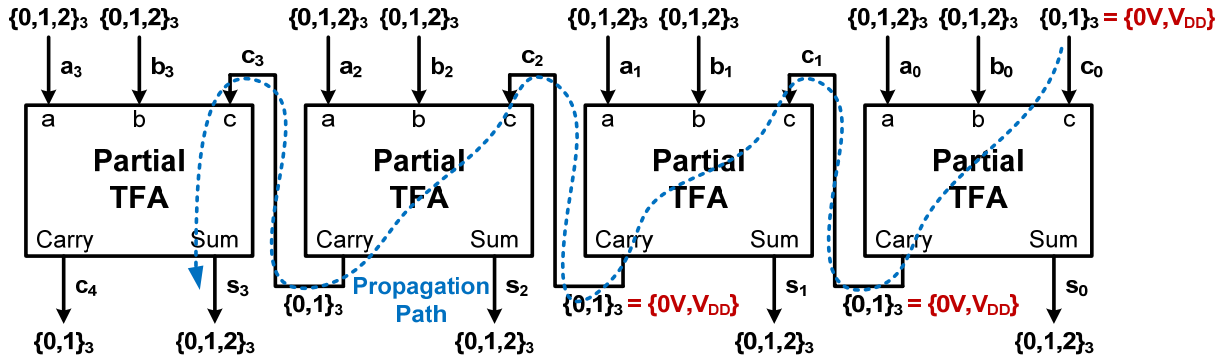


Fig. 23. A 4-digit RCA constructed by partial TFAs where $V(\text{Carry}='1') = V_{DD}$.

TABLE XVII: Simulation Results of 4-Digit RCA by the Simplified Partial TFAs

Simplified Partial TFAs of	Delay (ps)	Average Power (μW)	PDP (fJ)
[101] (Fig. 8)	74.609	6.1581	0.4594
[35] (Fig. 10)	86.646	2.4320	0.2107
[102] (Fig. 12)	90.390	4.7382	0.4283
[103] (Fig. 13)	59.485	2.9451	0.1752
[58] (Fig. 14)	73.097	6.1694	0.4509
[21] (Fig. 15)	79.400	2.0073	0.1594
[60] (Fig. 16)	263.74	6.9501	1.8330
[87] (Fig. 17)	42.893	5.8932	0.2527
[17] (Fig. 18)	36.623	2.1830	0.0799
[37]* (Fig. 19)	143.93	1.8263	0.2629

* We have not made any simplification to this design.

Here are some other noticeable observations when considering all of the experiments performed in this paper:

- The designs in [21] and [102] have the same logic style unless the latter employs two binary inverters in the middle. On the one hand, they provide high driving capability and boost performance when the adder cell drives a large output load (e.g. TFO4). On the other hand, they lengthen the critical path of the cell. This is the reason why the performance of the RCA constructed by [102] is not as satisfactory/fast as when the single-digit TFA is put under test in rigorous conditions. The structure of RCA does not burden a high load on a single TFA cell as TFO4 does.
- It might seem that TFAs made up of cascaded THAs are slower than direct designs. However, the designs in [17, 101, 102] are fairly fast. Moreover, they provide a kind of parallelism in the RCA scenario when the first THAs in each bit positions can perform simultaneous computations. This is one of the reasons why the RCA constructed by [17] is very fast.
- Once the ternary inputs are decoded, the employment of ternary gates is no longer needed, and binary gates can be replaced to improve performance. The TFA in [60] and its simplified version are good examples in this regard.
- The TFA in [60], which is composed of many binary components, consumes a lot of dynamic power. In addition, with an increase in the operating frequency, $P_{Dynamic}$ increases sharply compared to other designs

(Fig. 21). The main reason is that, unlike ternary logic, dynamic power is the dominant factor for power consumption in binary logic. Note that the slope in Fig. 22 is not as sharp as in Fig. 21 for this adder cell. The reason is that the capacitive loads are only added to the output nodes, *Sum* and *Carry*, whereas an increase in the operating frequency affects all of the internal nodes.

- The utilization of PTs is a helpful strategy to reduce the number of transistors, as it has led to fewer transistors in [37] and [58].
- The unbroken generation of $\frac{1}{2}V_{DD}$ by a constant voltage division is one the reasons why the TFA in [60] has the most power dissipation. In an alternative solution, voltage division can be limited to only when the output *Sum* is supposed to be '1'. Simulation results in Figs. 21 and 22 also confirm high static power dissipation for this design.

V. Conclusions and Future Works

A review of ternary adder cells, with a focus on TFA, has been conducted in this paper. Although the results were tabulated next to each other and one can compare the selected TFAs in this paper, we are not going to choose a specific logic family as the best option because each logic style has its advantages, disadvantages, and application. Moreover, it is neither fair nor precise to conclude from the simulation of a limited number of circuits that a logic family is superior to others. Such a firm conclusion needs far more simulations with more in-depth analyses, which can be done in future studies.

Another target of this paper was to reveal the shortcomings of the previous papers. The deficiencies exist not only in the environment where the previous TFAs have been simulated but also in how they have been designed. It has been shown in this paper that many transistors could have been eliminated from the previous TFAs by designing a partial TFA instead of a complete one. Furthermore, no voltage division is required in the *Carry* generator part. Such simplifications have been carried out in this paper, and simulation results show how efficient the simplified partial TFAs compared to their complete versions are.

Considerable efforts have been made on this topic; however, further attempts are still required to develop higher-performance ternary adders. A TFA with the faster operation, lower power consumption, and fewer transistors is needed to be considered a potential rival for the binary counterparts. It is a challenge that has not been resolved yet. Eventually, we must mention that multi- V_{DD} ternary circuits, which have been excluded in this review paper, might be a possible solution. Therefore, a comprehensive survey of multi- V_{DD} TFAs is worthy of conduct in the future.

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